IN THE CLAIMS

1-12. (*Canceled*).

13. (*Currently Amended*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating two or more parallel sets of megasonic waves in a cleaning fluid, the megasonic waves having a direction of travel and wave fronts that are generally perpendicular to the direction of travel;

immersing semiconductors in the cleaning fluid; and

moving the wafers in the cleaning fluid through said megasonic waves in a direction that is generally ~~transverse~~ perpendicular to the direction of travel of the megasonic waves and generally perpendicular to the wave fronts of the megasonic waves.

14. (*Original*) The method of claim 13 wherein the megasonic waves are generated across parallel regions of the fluid and the step of moving the wafers comprises reciprocating the wafers through said parallel regions.

15. (*Currently Amended*) A method for megasonic cleaning of semiconductor wafers disposed at least partially within a holder, the holder and

wafers disposed at least partially in a cleaning fluid within a container, the method comprising the steps of:

generating megasonic waves in the cleaning fluid ~~in a container~~;

intercepting the generated waves inside the container at a location between one or more sources of the megasonic waves and the holder, and dispersing the waves in a divergent manner; and

exposing the semiconductor wafers to the dispersed megasonic waves within the cleaning fluid.

16-26. (*Canceled*).

27. (*New*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating two or more parallel sets of megasonic waves in a cleaning fluid;

immersing semiconductors in the cleaning fluid; and

moving the wafers in the cleaning fluid through said megasonic waves in a direction that is generally transverse to the megasonic waves and generally perpendicular to faces of the wafers.